

TRANSISTOR(NPN)

FEATURES

Driver transistor

MARKING :1H

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	0.5	A
P_C	Collector Power Dissipation	300	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

SOT-23

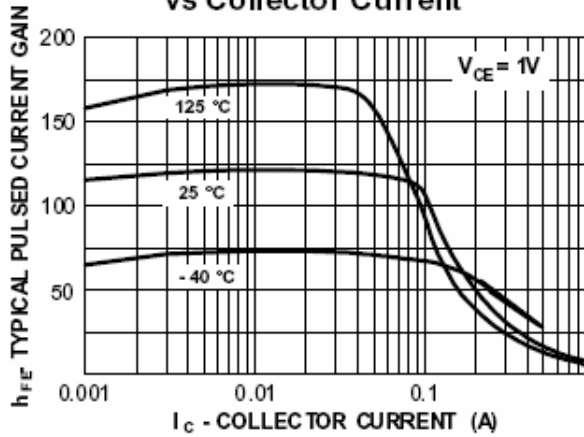


1. BASE
2. EMITTER
3. COLLECTOR

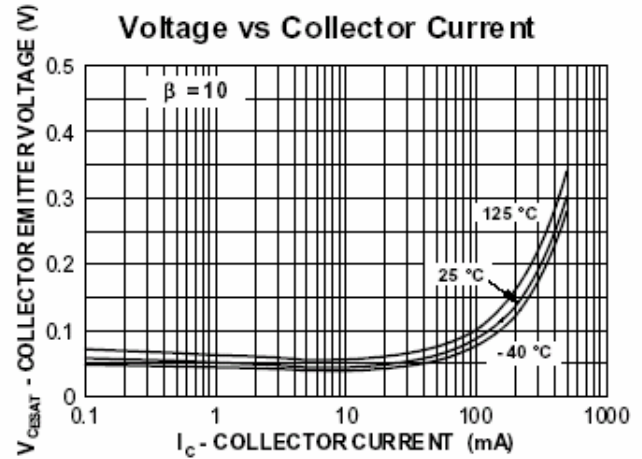
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}$, $I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=60\text{V}$, $I_B=0$			0.1	μA
Collector cut-off current	I_{EBO}	$V_{EB}=3\text{V}$, $I_C=0$			0.1	μA
DC current gain	h_{FE1}	$V_{CE}=1\text{V}$, $I_C=10\text{mA}$	100		400	
	h_{FE2}	$V_{CE}=1\text{V}$, $I_C=100\text{mA}$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}$, $I_B=10\text{mA}$			0.25	V
Base-emitter voltage	V_{BE}	$V_{CE}=1\text{V}$, $I_C=100\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=2\text{V}$, $I_C=10\text{mA}$ $f=100\text{MHz}$	100			MHz

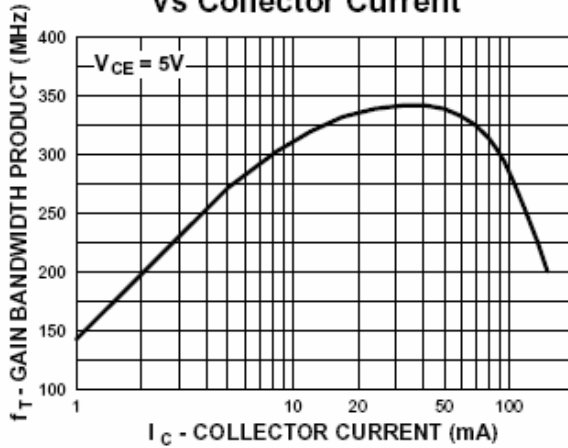
**Typical Pulsed Current Gain
vs Collector Current**



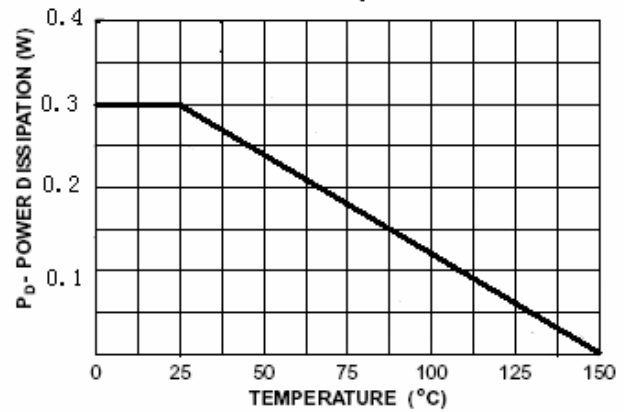
**Collector-Emitter Saturation
Voltage vs Collector Current**



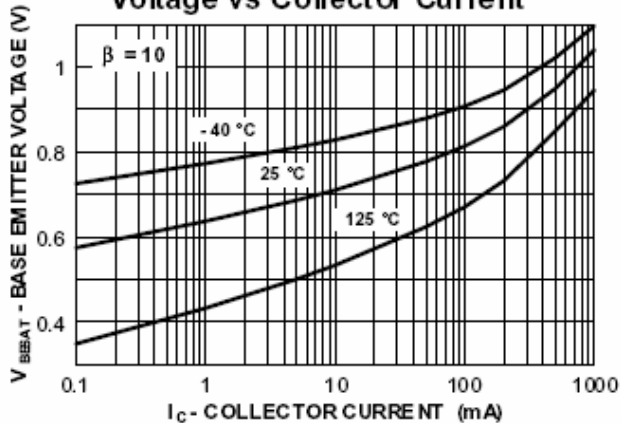
**Gain Bandwidth Product
vs Collector Current**



**Power Dissipation vs
Ambient Temperature**



**Base-Emitter Saturation
Voltage vs Collector Current**



**Base Emitter ON Voltage vs
Collector Current**

